

# 2N2913-2N2920

## NPN SILICON DUAL TRANSISTORS

### FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

### MAXIMUM RATINGS

Rating	Symbol	2N2913-2N2918	2N2919-2N2920	Unit
Collector emitter sustaining voltage	$V_{CEO}$	45	60	V
Collector base voltage	$V_{CBO}$	45	60	V
Emitter base voltage	$V_{EBO}$	6		V
Collector current	$I_C$	30		mA
Operating and storage temperature range	$T_J, T_{stg}$	-65 to +200		°C
		One side	Both sides	
Total power dissipation @ $T_A = 25^\circ\text{C}$ 2N2913-2N2920 Derate above $25^\circ\text{C}$	$P_D$	300 1.7	600 3.4	mW mW/°C
Total power dissipation @ $T_C = 25^\circ\text{C}$ 2N2913-2N2920 Derate above $25^\circ\text{C}$	$P_D$	750 4.3	1500 8.6	mW mW/°C

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-emitter sustaining voltage $I_C = 10\text{mA}, I_B = 0$	2N2913-2N2918 2N2919, 2N2920 $BV_{CEO(sus)}$	45 60	- 70	- -	V
Collector-base breakdown voltage $I_C = 10\mu\text{A}, I_E = 0$	2N2913-2N2918 2N2919, 2N2920 $BV_{CBO}$	45 60	- 90	- -	V
Emitter-base breakdown voltage $I_E = 10\mu\text{A}, I_C = 0$	$BV_{EBO}$	6	7	-	V
Collector cutoff current $V_{CE} = 5\text{V}, I_B = 0$	$I_{CEO}$	-	-	0.002	$\mu\text{A}$
Collector cutoff current $V_{CB} = 45\text{V}, I_E = 0$ $V_{CB} = 45\text{V}, I_E = 0, T_A = 150^\circ\text{C}$	2N2913-2N2918 2N2919, 2N2920 All types $I_{CBO}$	- - -	- - -	0.010 0.002 10	$\mu\text{A}$
Emitter cutoff current $V_{EB} = 5\text{V}, I_C = 0$	$I_{EBO}$	-	-	0.002	$\mu\text{A}$
Collector-emitter saturation voltage $I_C = 1.0\text{mA}, I_B = 0.1\text{mA}$	$V_{CE(sat)}$	-	-	0.35	V
Base-emitter on voltage $I_C = 100\mu\text{A}, V_{CE} = 5\text{V}$	$V_{BE(on)}$	-	-	0.7	V

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### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Min.	Typ.	Max.	Unit
ON-CHARACTERISTICS						
DC current gain *						
I <sub>C</sub> = 10μA, V <sub>CE</sub> = 5V	2N2913, 15, 17, 19	h <sub>FE</sub> *	60	-	240	
	2N2914, 16, 18, 20		150	-	600	
I <sub>C</sub> = 10μA, V <sub>CE</sub> = 5V, T <sub>A</sub> = -55°C	2N2913, 15, 17, 19		15	-	-	
	2N2914, 16, 18, 20		30	-	-	
I <sub>C</sub> = 100μA, V <sub>CE</sub> = 5V	2N2913, 15, 17, 19		100	-	-	
	2N2914, 16, 18, 20		225	-	-	
I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 5V	2N2913, 15, 17, 19		150	-	-	
	2N2914, 16, 18, 20		300	-	-	
SMALL SIGNAL CHARACTERISTICS						
Output capacitance		C <sub>ob</sub>	-	4.0	6.0	pF
V <sub>CB</sub> = 5.0V, I <sub>E</sub> = 0, f = 140kHz						
High frequency current gain		h <sub>fe</sub>	3.0	-	-	-
I <sub>C</sub> = 500μA, V <sub>CE</sub> = 5.0V, f = 20MHz						
Input impedance		h <sub>ib</sub>	25	28	32	Ω
I <sub>C</sub> = 1.0mA, V <sub>CB</sub> =5.0V, f = 1.0kHz						
Output admittance		h <sub>ob</sub>	-	-	1.0	μmhos
I <sub>C</sub> = 1.0mA, V <sub>CB</sub> =5.0V, f = 1.0kHz						
Noise figure		NF				
I <sub>C</sub> = 10μA, V <sub>CE</sub> = 5.0V, R <sub>S</sub> = 10kΩ, f = 1.0kHz, BW = 200Hz	2N2914, 16, 18, 20		-	2.0	3.0	dB
	2N2913, 15, 17, 19		-	3.0	4.0	
I <sub>C</sub> = 10μA, V <sub>CE</sub> = 5.0V, R <sub>S</sub> = 10kΩ, f = 10Hz – 15.7kHz, BW = 10kHz	2N2914, 16, 18, 20		-	2.0	3.0	
	2N2913, 15, 17, 19		-	3.0	4.0	
DC current gain ratio**	2N2917, 18	h <sub>FE1</sub> /h <sub>FE2</sub> *	0.8	-	1.0	
I <sub>C</sub> = 100μA, V <sub>CE</sub> = 5.0V	2N2915, 16, 19, 20	*	0.9	-	1.0	
Base voltage differential		V <sub>BE1</sub> -V <sub>BE2</sub>				
I <sub>C</sub> = 10μA to 1.0mA, V <sub>CE</sub> = 5.0V	2N2917, 18		-	-	10	mV
	2N2915, 16, 19, 20		-	-	5.0	
I <sub>C</sub> = 100μA, V <sub>CE</sub> = 5.0V	2N2917, 18		-	-	5.0	
	2N2915, 16, 19, 20		-	-	3.0	
Base voltage differential gradient		Δ V <sub>BE1</sub> - V <sub>BE2</sub>				
I <sub>C</sub> = 100μA, V <sub>CE</sub> = 5.0V, T <sub>A</sub> = -55 to 25°C	2N2917, 18		-	-	1.6	mV
	2N2915, 16, 19, 20		-	-	0.8	
I <sub>C</sub> = 100μA, V <sub>CE</sub> = 5.0V, T <sub>A</sub> = 25 to 125°C	2N2917, 18		-	-	2.0	
	2N2915, 16, 19, 20		-	-	1.0	

\*Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%.

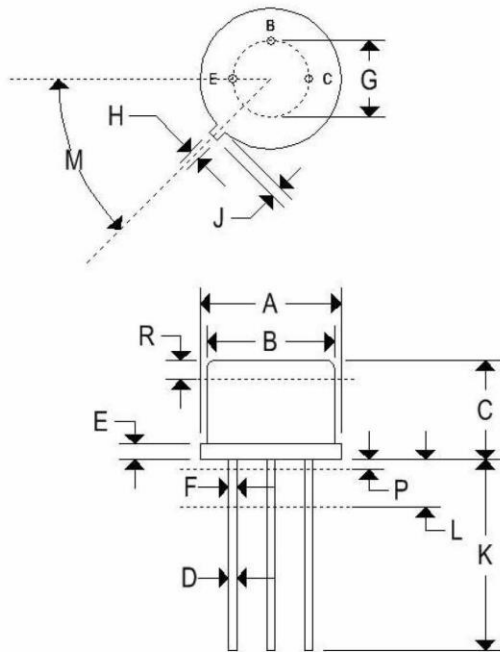
\*\*The lowest h<sub>FE</sub> reading is taken as h<sub>FE1</sub> for this ratio.

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### MECHANICAL CHARACTERISTICS

Case	TO-39
Marking	Alpha-numeric
Polarity	See below



	TO-39			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.350	0.370	8.890	9.400
B	0.315	0.335	8.000	8.510
C	0.240	0.260	6.10	6.60
D	0.016	0.021	0.406	0.533
E	0.009	0.125	0.2269	3.180
F	0.016	0.019	0.406	0.533
G	0.190	0.210	4.830	5.33
H	0.028	0.034	0.711	0.864
J	0.029	0.040	0.737	1.020
K	0.500	-	12.700	-
L	0.250	-	6.350	-
M	45° NOM		45° NOM	
P	-	0.050	-	1.270
Q	90° NOM		90° NOM	
R	0.100	-	2.540	-